



DMNH6012LK3Q

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	12mΩ @ V _{GS} = 10V	80A
000	$18m\Omega @ V_{GS} = 4.5V$	70A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC/DC Converters

60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Features

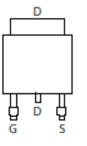
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures more Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

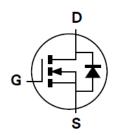
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



Equivalent Circuit

Ordering Information (Note 5)

	Part Number	Case	Packaging	
DMNH6012LK3Q-13		TO252 (DPAK)	2500/Tape & Reel	
Notes: 1 ELL Directive 2002/05/EC (PoHS) & 2011/65/ELL (PoHS 2) compliant All applicable PoHS exemptions applied				

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

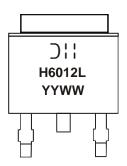
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



):: =Manufacturer's Marking
H6012L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 8), V _{GS} = 10V	I _D	80 60	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	120	A
Maximum Continuous Body Diode Forward Current (Note 8)	I _S	80	A
Avalanche Current, L = 0.1mH (Note 9)	I _{AS}	45	A
Avalanche Energy, L = 0.1mH (Note 9)	Eas	100	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	PD	2.0	W	
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ hetaJA}$	74	°C/W	
Total Power Dissipation (Note 7)	PD	3.8	W	
Thermal Resistance, Junction to Ambient (Note 7) Steady State		$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction to Case (Note 8)	$R_{\theta JC}$	1.2	C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)	0,			inax	0		
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	—	V	$V_{GS} = 0V, I_{D} = 250 \mu A$	
Zero Gate Voltage Drain Current, TJ = +25°C	I _{DSS}	_	_	1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)						-	
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	8	12	mΩ	V _{GS} = 10V, I _D = 25A	
	R _{DS(ON)}	_	10	18		$V_{GS} = 4.5V, I_D = 25A$	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	V _{GS} = 0V, I _S = 1.7A	
DYNAMIC CHARACTERISTICS (Note 11)						-	
Input Capacitance	C _{iss}	_	1926	—	pF		
Output Capacitance	Coss	_	330	—	pF	$V_{DS} = 30V, V_{GS} = 0V,$ - f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	112	—	pF		
Gate Resistance	Rg	_	2.0	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	16.3	—	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	_	35.2	—	nC		
Gate-Source Charge	Q _{gs}	—	7.6	—	nC	$-V_{DS} = 30V, I_{D} = 25A$	
Gate-Drain Charge	Q _{gd}	—	6.9	—	nC		
Turn-On Delay Time	t _{D(ON)}	_	6.4	_	ns		
Turn-On Rise Time	t _R	_	11.9	—	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_g = 3\Omega, I_D = 25A$	
Turn-Off Delay Time	t _{D(OFF)}	_	16.5	—	ns		
Turn-Off Fall Time	t _F	_	5	—	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	28	—	ns	I _F = 25A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	23	_	nC	I _F = 25A, di/dt = 100A/µs	

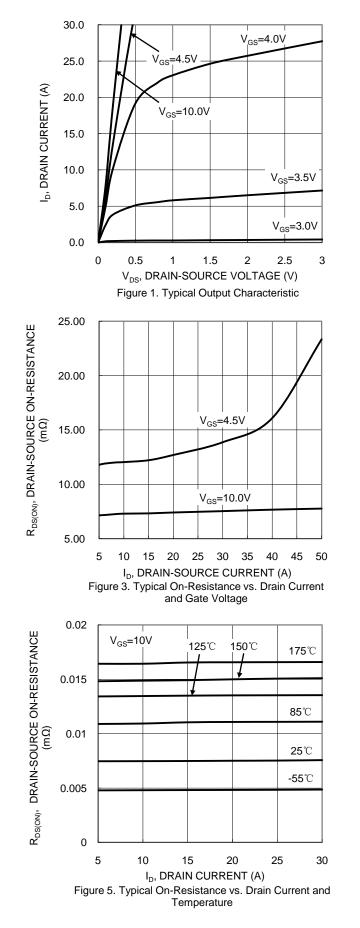
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

8. Thermal resistance from junction to soldering point (on the exposed drain pad). 9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}$ C. 10. Short duration pulse test used to minimize self-heating effect. 11. Guaranteed by design. Not subject to product testing.



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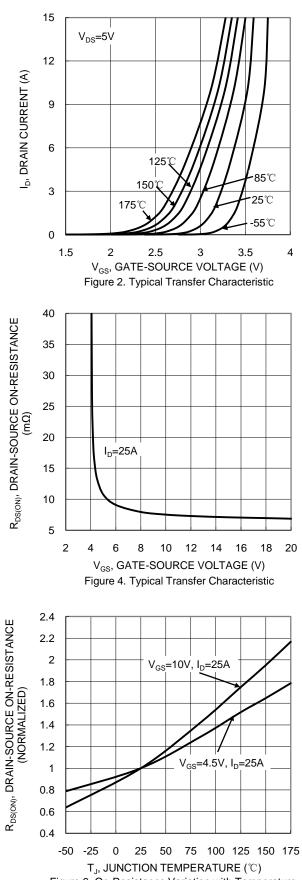
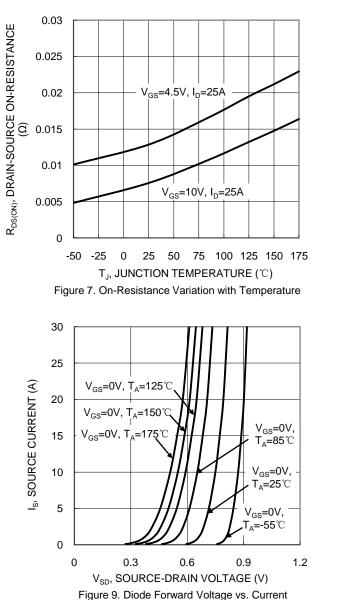


Figure 6. On-Resistance Variation with Temperature

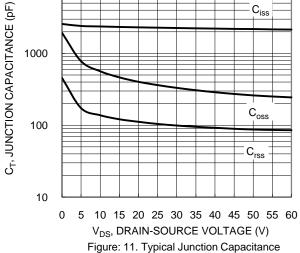
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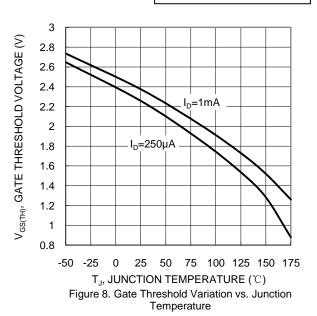


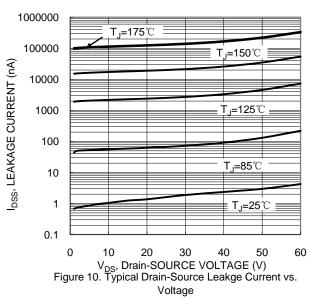


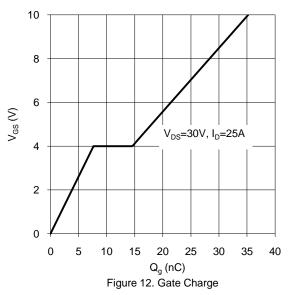


10000 f=1MHz C_{iss}



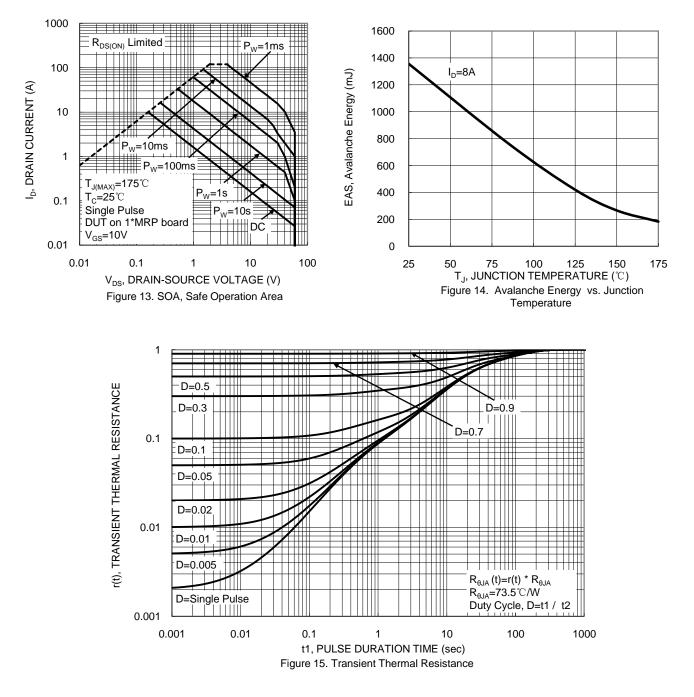






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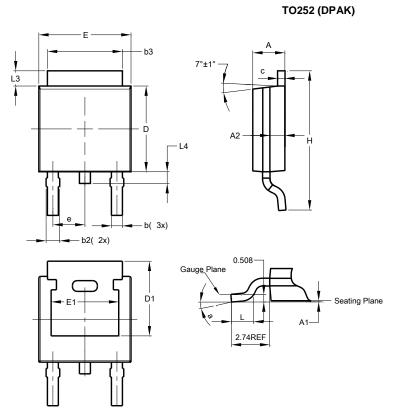






Package Outline Dimensions

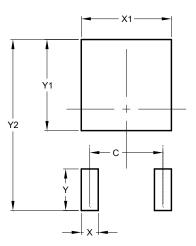
Please see http://www.diodes.com/package-outlines.html for the latest version.



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
e	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)				
С	4.572				
Х	1.060				
X1	5.632				
Y	2.600				
Y1	5.700				
Y2	10.700				

TO252 (DPAK)



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